

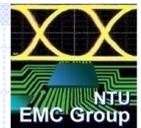
Microwave Filter Design

Chp5. Lowpass Filters

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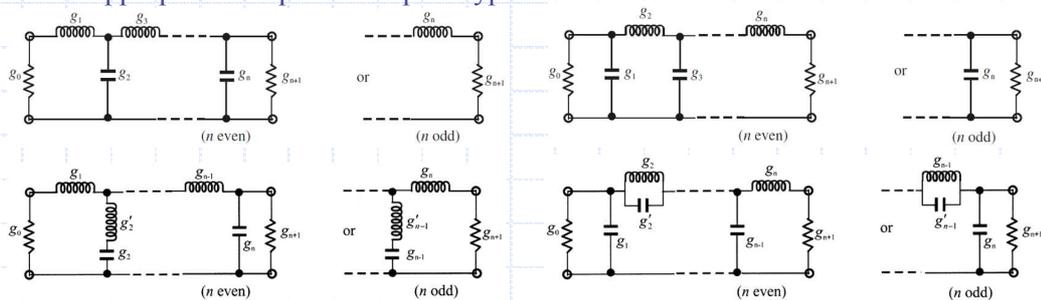
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Lowpass Filters

Design steps

- Select an appropriate lowpass filter prototype

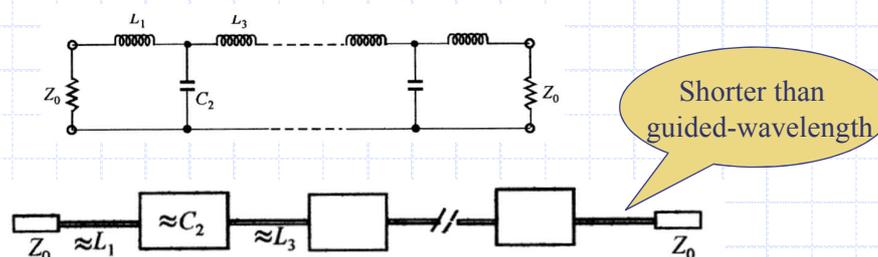


- The choice of the type of response including passband ripple and the number of reactive elements
 - ◆ Butterworth (Maximally Flat) Response
 - ◆ Chebyshev (Equal-Ripple) Response
 - ◆ Gaussian Response
 - ◆ Elliptic Function Response
- Find an appropriate microstrip realization
 - ◆ Stepped-Impedance LPF
 - ◆ LPF using open-circuited stubs
 - ◆ Semilumped LPF having finite-frequency attenuation poles

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Stepped-Impedance LPF

- General structure – cascaded structure of high- and low-impedance TML



- Design considerations

- ◆ $Z_{0C} < Z_0 < Z_{0L}$, where Z_{0C} and Z_{0L} denote the characteristic impedances of the low and high impedance lines, respectively, and Z_0 is the source impedance, which is usually 50 ohms.
- ◆ Lower Z_{0C} results in a better approximation of a lumped-element capacitor, but the resulting line width W_C must not allow any **transverse resonance** to occur at operation frequency.
- ◆ Higher Z_{0L} leads to a better approximation of a lumped-element inductor, but Z_{0L} must not be so high that its **fabrication** become difficult, or its **current-carrying capability** becomes a limitation.

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Example - Stepped-impedance LPF

- Design a three-order LPF with 0.1 dB ripple and cutoff frequency of 1 GHz. The source/load impedance of the filter is 50 Ω .

- ◆ Step 1 – Find out the required L/C element values

For passband ripple $L_{Ar} = 0.1$ dB ($g_0 = 1.0, \Omega_c = 1$)

n	g_1	g_2	g_3	g_4	g_5	g_6
1	0.3052	1.0				
2	0.8431	0.6220	1.3554			
3	1.0316	1.1474	1.0316	1.0		
4	1.1088	1.3062	1.7704	0.8181	1.3554	

$$L_1 = L_3 = \left(\frac{Z_0}{g_0} \right) \left(\frac{\Omega_c}{2\pi f_c} \right) g_1 = \underline{8.209 \times 10^{-9} \text{ H}}$$

$$C_2 = \left(\frac{g_0}{Z_0} \right) \left(\frac{\Omega_c}{2\pi f_c} \right) g_2 = \underline{3.652 \times 10^{-12} \text{ F}}$$

- ◆ Step 2 – Choose the adequate design parameters of microstrip lines

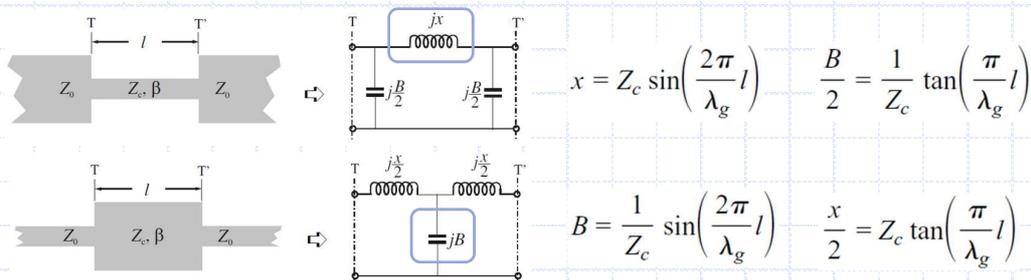
Characteristic impedance (ohms)	$Z_{0C} = 24$	$Z_0 = 50$	$Z_{0L} = 93$
Guided wavelengths (mm)	$\lambda_{gC} = 105$	$\lambda_{g0} = 112$	$\lambda_{gL} = 118$
Microstrip line width (mm)	$W_C = 4.0$	$W_0 = 1.1$	$W_L = 0.2$

fabricated on a substrate with a relative dielectric constant of 10.8 and a thickness of 1.27 mm.

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Example - Stepped-impedance LPF

- ◆ Step 3 – physical length of the high- and low-impedance lines



- Initial guess for the physical length

$$l_L = \frac{\lambda_{gL}}{2\pi} \sin^{-1}\left(\frac{\omega_c L}{Z_{0L}}\right) \quad \Rightarrow \quad l_L = 11.04 \text{ mm}$$

$$l_C = \frac{\lambda_{gC}}{2\pi} \sin^{-1}(\omega_c C Z_{0C}) \quad \Rightarrow \quad l_C = 9.75 \text{ mm}$$

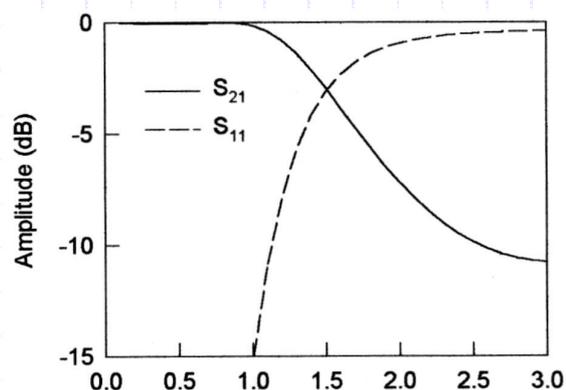
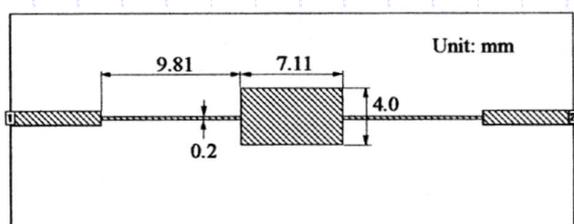
- Compensate the parasitic elements

$$\omega_c L = Z_{0L} \sin\left(\frac{2\pi l_L}{\lambda_{gL}}\right) + Z_{0C} \tan\left(\frac{\pi l_C}{\lambda_{gC}}\right) \quad \Rightarrow \quad l_L = 9.81 \text{ mm}$$

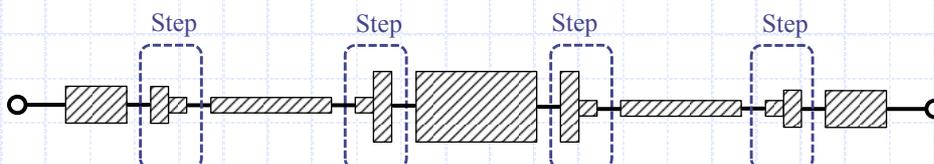
$$\omega_c C = \frac{1}{Z_{0C}} \sin\left(\frac{2\pi l_C}{\lambda_{gC}}\right) + 2 \times \frac{1}{Z_{0L}} \tan\left(\frac{\pi l_L}{\lambda_{gL}}\right) \quad \Rightarrow \quad l_C = 7.11 \text{ mm}$$

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Example - Stepped-impedance LPF



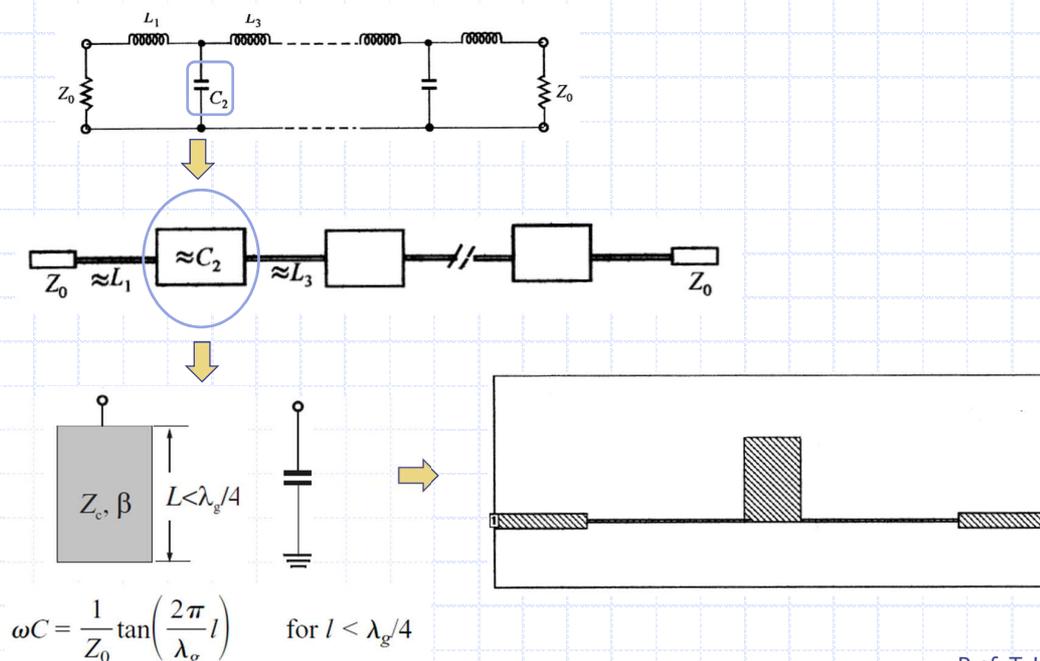
- ◆ Step 4 – take discontinuities into account as circuit simulator is used



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LPF using open-circuited stubs

- General structure – high-impedance TML and open-circuited stubs



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Example

- LPF with open-circuited stubs

- Design a three-order LPF with 0.1 dB ripple and cutoff frequency of 1 GHz. The source/load impedance of the filter is 50 Ω .

- ◆ Step 1 – Find out the required L/C element values

For passband ripple $L_{Ar} = 0.1$ dB ($g_0 = 1.0, \Omega_c = 1$)

n	g_1	g_2	g_3	g_4	g_5	g_6
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$$L_1 = L_3 = \left(\frac{Z_0}{g_0}\right) \left(\frac{\Omega_c}{2\pi f_c}\right) g_1 = \underline{8.209 \times 10^{-9} \text{ H}}$$

$$C_2 = \left(\frac{g_0}{Z_0}\right) \left(\frac{\Omega_c}{2\pi f_c}\right) g_2 = \underline{3.652 \times 10^{-12} \text{ F}}$$

- ◆ Step 2 – Choose the adequate design parameters of microstrip lines

Characteristic impedance (ohms)	$Z_{0C} = 24$	$Z_0 = 50$	$Z_{0L} = 93$
Guided wavelengths (mm)	$\lambda_{gC} = 105$	$\lambda_{g0} = 112$	$\lambda_{gL} = 118$
Microstrip line width (mm)	$W_C = 4.0$	$W_0 = 1.1$	$W_L = 0.2$

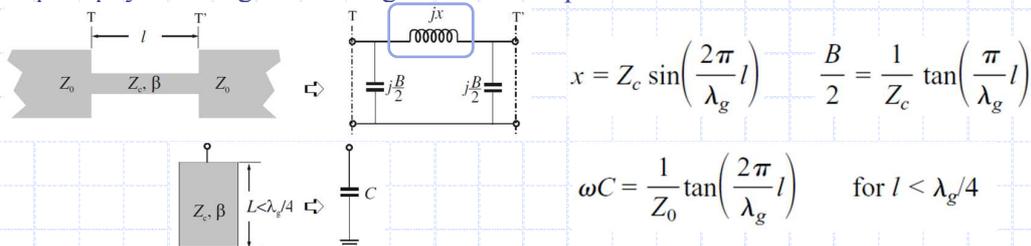
fabricated on a substrate with a relative dielectric constant of 10.8 and a thickness of 1.27 mm.

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Example

- LPF with open-circuited stubs

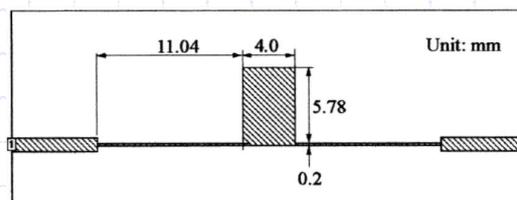
- Step 3 – physical length of the high- and low-impedance lines



- Initial guess for the physical length

$$l_L = \frac{\lambda_{gL}}{2\pi} \sin^{-1}\left(\frac{\omega_c L}{Z_{0L}}\right) = 11.04 \text{ mm}$$

$$l_C = \frac{\lambda_{gC}}{2\pi} \tan^{-1}(\omega_c C Z_{0C}) = 8.41 \text{ mm}$$



- Compensate the discontinuities

- parasitic effect on high-impedance line

$$\omega_c C = \frac{1}{Z_{0C}} \tan\left(\frac{2\pi l_C}{\lambda_{gC}}\right) + 2 \times \frac{1}{Z_{0L}} \tan\left(\frac{\pi l_L}{\lambda_{gL}}\right) \Rightarrow l_C = 6.28 \text{ mm}$$

- open-end

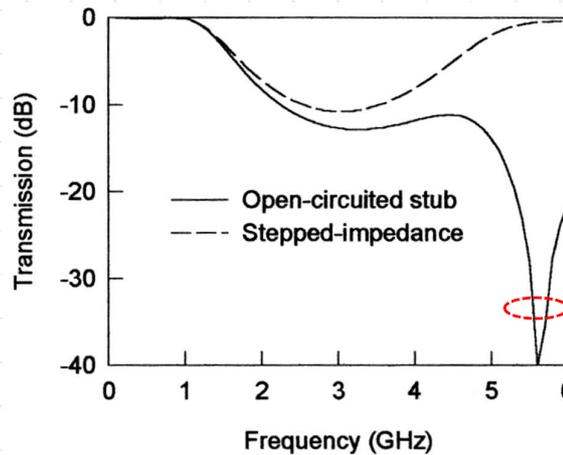
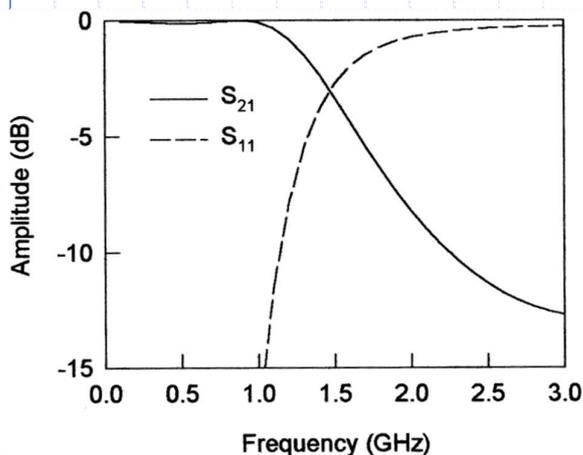
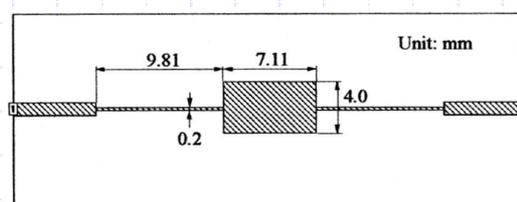
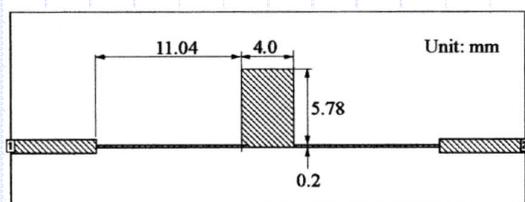
$$\Delta l = \frac{c Z_c C_p}{\sqrt{\epsilon_{re}}} = 0.5 \text{ mm} \Rightarrow l_C = 6.28 - 0.5 = 5.78 \text{ mm}$$

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Example

- Results and comparisons

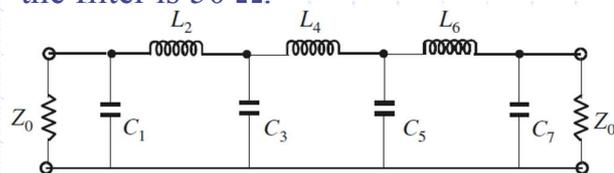
- LPF with open-circuited stubs can exhibit a better stopband characteristic.



Example

- LPF with open-circuited stubs

- To obtain a sharper rate of cutoff, a seven-order LPF is designed with 0.1 dB ripple and cutoff frequency of 1 GHz. The source/load impedance of the filter is 50 Ω.



$$Z_0 = 50 \text{ ohm}$$

$$L_2 = L_6 = 11.322 \text{ nH}$$

$$L_4 = 12.52 \text{ nH}$$

$$C_1 = C_7 = 3.7596 \text{ pF}$$

$$C_3 = C_5 = 6.6737 \text{ pF}$$

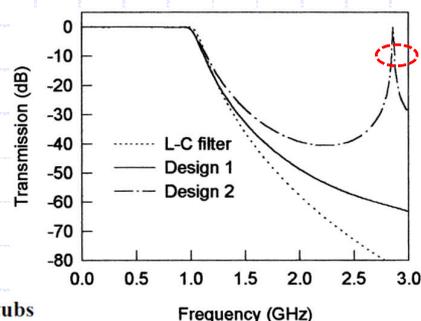
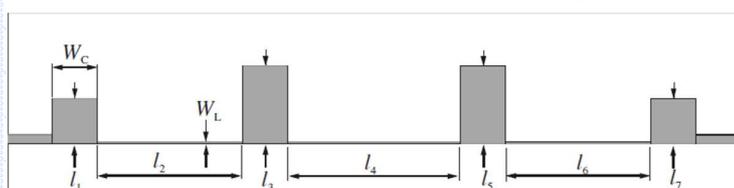


TABLE 5.2 Two microstrip lowpass filter designs with open-circuited stubs

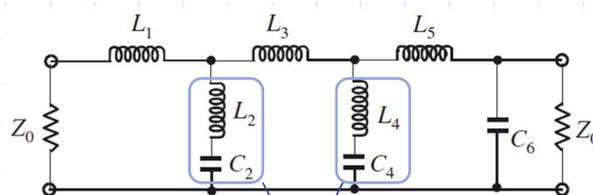
Substrate ($\epsilon_r = 10.8, h = 1.27 \text{ mm}$) $W_C = 5 \text{ mm}$	$l_1 = l_7$ (mm)	$l_2 = l_6$ (mm)	$l_3 = l_5$ (mm)	l_4 (mm)
Design 1 ($W_L = 0.1 \text{ mm}$)	5.86	13.32	9.54	15.09
Design 2 ($W_L = 0.2 \text{ mm}$)	5.39	16.36	8.67	18.93

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LPF with attenuation poles (transmission zeros)

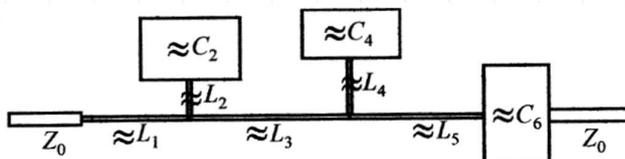
- To obtain an sharper rate of cutoff, attenuation poles are required to achieve the frequency response.

- ◆ Prototype filter with elliptic function response



Attenuation pole

- ◆ General structure – cascaded structure of open-circuited stubs, high- and low-impedance TML



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Example

- LPF with attenuation poles

- Design a six-order elliptic LPF with a passband ripple $L_{Ar} = 0.18$ dB and a minimum stopband attenuation $L_{As} = 38.1$ dB at $\Omega_s = 1.194$ for cutoff $\Omega_c = 1$. The filter is designed at cutoff frequency $f_c = 1$ GHz and the source/load impedance of the filter is 50Ω .

- Step 1 – Find out the required L/C element values

56	1.252	921	42.7	0.8705	0.3221	1.147	1.645	294	1.269	0.5941	1.024	1.281	971	1.172	1.140	56
57	1.237	179	41.5	0.8387	0.3377	1.132	1.617	530	1.249	0.6274	0.9957	1.265	189	1.159	1.139	57
58	1.222	145	40.4	0.8466	0.3541	1.116	1.590	725	1.229	0.6629	0.9668	1.249	136	1.145	1.138	58
59	1.207	787	39.3	0.8342	0.3712	1.100	1.564	828	1.209	0.7008	0.9375	1.233	777	1.131	1.137	59
60	1.194	077	38.1	0.8214	0.3882	1.084	1.539	791	1.188	0.7413	0.9077	1.219	083	1.117	1.136	60
61	1.180	985	37.0	0.8081	0.4081	1.067	1.515	571	1.167	0.7848	0.8775	1.205	023	1.103	1.134	61
62	1.168	486	35.9	0.7945	0.4280	1.049	1.492	126	1.146	0.8317	0.8468	1.191	572	1.088	1.133	62
63	1.156	557	34.8	0.7804	0.4490	1.032	1.469	414	1.125	0.8823	0.8157	1.178	704	1.074	1.131	63
64	1.145	175	33.7	0.7659	0.4712	1.013	1.447	401	1.103	0.9372	0.7843	1.166	396	1.058	1.130	64
65	1.134	320	32.6	0.7509	0.4947	0.9940	1.426	049	1.081	0.9970	0.7524	1.154	626	1.043	1.128	65
θ	Ω_s	A_s [dB]	L_1	L_2	C_2	Ω_s	L_3	L_4	C_4	Ω_s	L_5	C_5	θ			

$$g_0 = g_7 = 1.000$$

$$g_{L1} = g_1 = 0.8214$$

$$g_{L2} = g'_2 = 0.3892$$

$$g_{C2} = g_2 = 1.0840$$

$$g_{L3} = g_3 = 1.1880$$

$$g_{L4} = g'_4 = 0.7413$$

$$g_{C4} = g_4 = 0.9077$$

$$g_{L5} = g_5 = 1.1170$$

$$g_{C6} = g_6 = 1.1360$$

$$L_i = \frac{1}{2\pi f_c} Z_0 g_{Li}$$

$$C_i = \frac{1}{2\pi f_c} \frac{1}{Z_0} g_{Ci}$$

$$L_1 = 6.53649 \text{ nH}$$

$$L_3 = 9.45380 \text{ nH}$$

$$L_5 = 8.88880 \text{ nH}$$

$$C_6 = 3.61600 \text{ pF}$$

$$L_2 = 3.09716 \text{ nH}$$

$$C_2 = 3.45048 \text{ pF}$$

$$L_4 = 5.89908 \text{ nH}$$

$$C_4 = 2.88930 \text{ pF}$$

Attenuation poles

$$f_{p1} = \frac{1}{2\pi \sqrt{L_4 C_4}} = 1.219 \text{ GHz}$$

$$f_{p2} = \frac{1}{2\pi \sqrt{L_2 C_2}} = 1.540 \text{ GHz}$$

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Example

- LPF with attenuation poles

- Step 2 – Choose the adequate design parameters of microstrip lines

Characteristic impedance (ohms)	$Z_{0C} = 14$	$Z_0 = 50$	$Z_{0L} = 93$
Microstrip line width (mm)	$W_C = 8.0$	$W_0 = 1.1$	$W_L = 0.2$
Guided wavelength (mm) at f_c	$\lambda_{gC}(f_c) = 101$	$\lambda_{g0} = 112$	$\lambda_{gL}(f_c) = 118$
Guided wavelength (mm) at f_{p1}	$\lambda_{gC}(f_{p1}) = 83$		$\lambda_{gL}(f_{p1}) = 97$
Guided wavelength (mm) at f_{p2}	$\lambda_{gC}(f_{p2}) = 66$		$\lambda_{gL}(f_{p2}) = 77$

- Step 3 – Initial physical length of the high- and low-impedance lines

$$l_{Li} = \frac{\lambda_{gL}(f_c)}{2\pi} \sin^{-1} \left(2\pi f_c \frac{L_i}{Z_{0L}} \right)$$

$$l_{Ci} = \frac{\lambda_{gC}(f_c)}{2\pi} \sin^{-1} (2\pi f_c Z_{0C} C_i)$$

$$l_{L1} = 8.59$$

$$l_{L2} = 3.96$$

$$l_{L3} = 13.01$$

$$l_{C2} = 4.96$$

$$l_{L5} = 12.10$$

$$l_{L4} = 7.70$$

$$l_{C6} = 5.20$$

$$l_{C4} = 4.13$$

- Step 4 – Compensate the parasitic elements

1. For L_5 and C_6

$$2\pi f_c L_5 = Z_{0L} \sin \left(\frac{2\pi l_{L5}}{\lambda_{gL}(f_c)} \right) + Z_{0C} \tan \left(\frac{\pi l_{C6}}{\lambda_{gC}(f_c)} \right)$$

$$2\pi f_c C_6 = \frac{1}{Z_{0C}} \sin \left(\frac{2\pi l_{C6}}{\lambda_{gC}(f_c)} \right) + \frac{1}{Z_{0L}} \tan \left(\frac{\pi l_{L5}}{\lambda_{gL}(f_c)} \right)$$

$$l_{L5} = 11.62 \text{ mm}$$

$$l_{C6} = 4.39 \text{ mm}$$

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Example

- LPF with attenuation poles

- ◆ Step 4 – Compensate the parasitic elements
- 2. For L_2 and C_2 or L_4 and C_4 (fixed l_{L1} , l_{L2} , and l_{L3})

$$\frac{1}{(2\pi f L_2) - 1/(2\pi f C_2)} = B_2(f) + \Delta B_{123}(f) \quad \text{for } f = \underline{f_c} \text{ and } \underline{f_{p2}} \quad \Rightarrow \quad \begin{aligned} l_{L2} &= 2.98 \text{ mm} \\ l_{C2} &= 5.61 \text{ mm} \end{aligned}$$

where

$$B_2(f) = \frac{1}{Z_{0L} \sin\left(\frac{2\pi l_{L2}}{\lambda_{gL}(f)}\right) + Z_{0C} \tan\left(\frac{\pi l_{C2}}{\lambda_{gC}(f)}\right) - \frac{1}{\frac{1}{Z_{0C}} \sin\left(\frac{2\pi l_{C2}}{\lambda_{gC}(f)}\right) + \frac{1}{Z_{0L}} \tan\left(\frac{\pi l_{L2}}{\lambda_{gL}(f)}\right)}}$$

$$\Delta B_{123}(f) = \frac{1}{Z_{0L}} \tan\left(\frac{\pi l_{L1}}{\lambda_{gL}(f)}\right) + \frac{1}{Z_{0L}} \tan\left(\frac{\pi l_{L2}}{\lambda_{gL}(f)}\right) + \frac{1}{Z_{0L}} \tan\left(\frac{\pi l_{L3}}{\lambda_{gL}(f)}\right)$$

The same method can be applied to L_4 and C_4 and the corrected length are $l_{L4} = 6.49$ mm and $l_{C4} = 4.24$ mm.

- 3. l_{C2} and l_{C4} on open-end effect

$$\Delta l = \frac{cZ_c C_p}{\sqrt{\epsilon_{re}}} = 0.54 \text{ mm} \quad \Rightarrow \quad \begin{aligned} l_{C2} &= 5.61 - 0.54 = 5.07 \text{ mm} \\ l_{C4} &= 4.24 - 0.54 = 3.70 \text{ mm} \end{aligned}$$

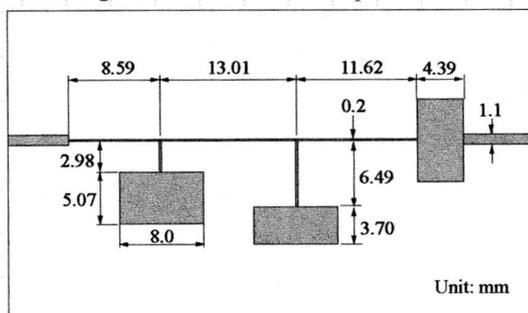
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Example

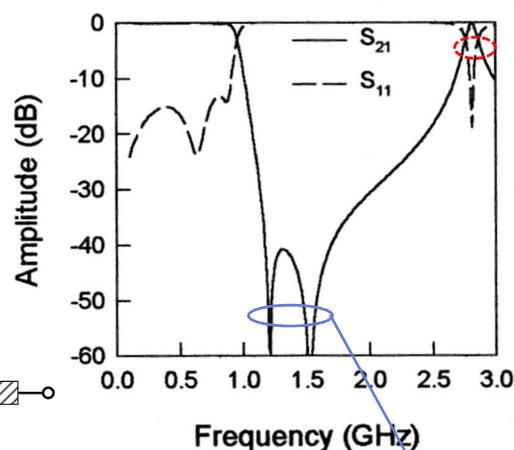
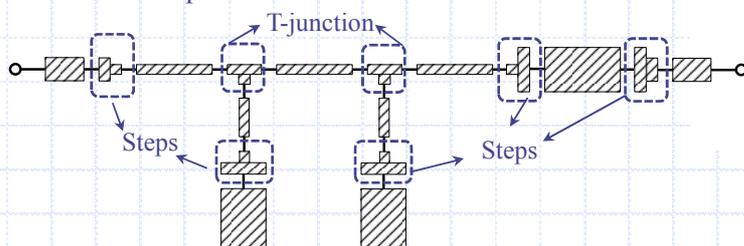
- LPF with attenuation poles

- A sharp rate of cutoff with two attenuation poles is designed

- ◆ The unwanted transmission peak could be moved away up to a higher frequency if higher characteristic impedance could be used for the inductive lines.



- ◆ Step 5 – take discontinuities into account



Attenuation poles

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HW II

Please design a LPF based on Chebyshev prototype with following specifications:

1. Passband ripple < 0.0432 dB
2. Cutoff frequency : 1 GHz
3. Insertion loss > 30 dB at 3 GHz.

The properties of the substrate is FR4 with $\epsilon_r = 4.2$ and loss tangent 0.01.

The substrate thickness is 1.6 mm. The high and low impedance used in this design is 90 ohm and 25 ohm, respectively. (Note: Please consider the parasitic effects and discontinuities)

- a. Please decide the order of the LPF and calculate the lumped element values of L and C.
- b. Based on step impedance approach, please plot the layout of the LPF, and calculate (and denote) the corresponding geometry dimensions.
- c. Plot the return loss and insertion loss for the designed LPF using ADS.
- d. Simulate the return loss and insertion loss for the designed LPF using full-wave simulator (CST or HFSS), and compare the results with those modeled in (c). Please also discuss the reasons for the discrepancy between them.
- e. Based on the open-circuited stubs approach, please repeat steps (b) to (d).